Linear IC Converter

CMOS

D/A Converter for Digital Tuning

(12-channel, 8-bit, on-chip OP amp, low-voltage)

MB88346L

DESCRIPTION

The Fujitsu Microelectronics MB88346L is a 12-channel 8-bit D/A converter capable of low-voltage operation that has amplifiers built into each of the 12 analog output lines to deliver heavy-current drive capability.

The use of serial data input means that only three control lines are required, and enables cascade connection of multiple MB88346L chips.

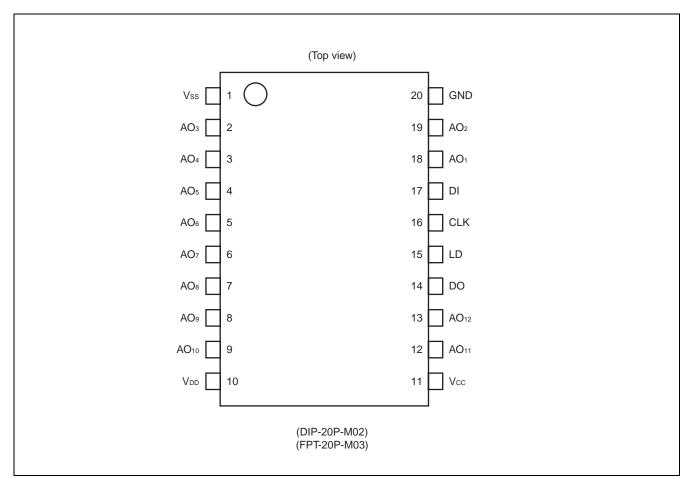
The MB88346L is suitable for applications such as electronic volume controls and replacing trimmer potentiometers in tuning systems. In addition, the MB88346L is both function-compatible and pin-compatible the currently used MB88346B, making it easy to reduce the voltage level of a system by simply replacing the MB88346B with the MB88346L.

■ FEATURES

- Low voltage operation (Vcc/Vpb : 2.7 V to 3.6 V)
- Ultra-low power consumption (0.5 mW/ch at Vcc = 3 V)
- Ultra-compact space-saving package lineup (SSOP-20)
- Contains 12-channel R-2R type 8-bit D/A converter
- On-chip analog output amps (sink current max. 1.0 mA, source current max. 1.0 mA)
- Analog output range from 0 to Vcc
- Two separate power supply/ground lines for MCU interface block/operational amplifier output buffer block and D/A converter block
- Serial data input: maximum operating speed 2.5 MHz
 (maximum operating speed in cascade connection is 1.5 MHz)
- CMOS process
- Package lineup includes DIP 20-pin, SSOP 20-pin



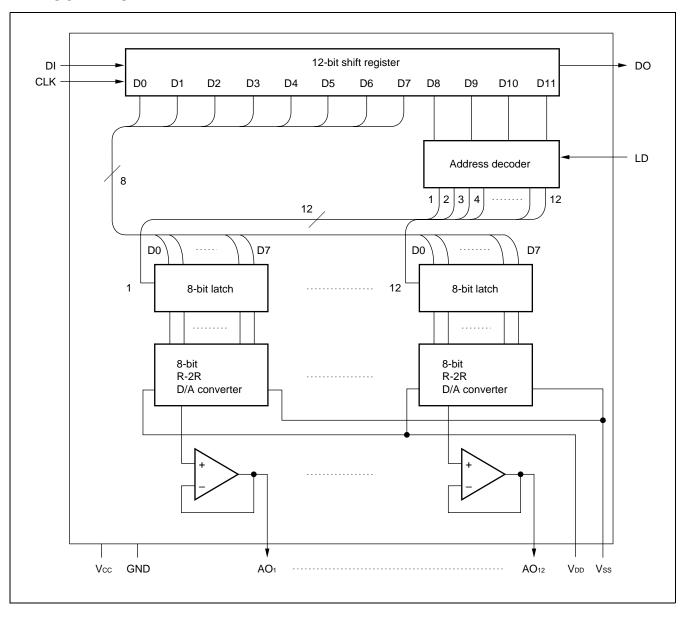
■ PIN ASSIGNMENT



■ PIN DESCRIPTION

Pin No.	Symbol	I/O	Function
17	DI	I	Serial address/data input to the internal 12-bit shift register: The address/data format is that upper 4 bits (D11 to D8) indicate an address and lower 8 bits (D7 to D0) indicate data. The D11 (MSB) is the first-in bit and D0 (LSB) is the last-in bit.
14	DO	0	Outputs MSB bit data from 12-bit shift register.
16	CLK	I	Shift clock input to the internal 12-bit shift register: At the rising edge of CLK data on the DI pin is shifted into the LSB of the shift register and contents of the shift register are shifted right (to the MSB).
15	LD	I	Load strobe input for a 12-bit address/data: A high level on the LD pin latches a 4-bit address (upper 4 bits: D11 to D8) of the internal 12-bit shift register into the internal address decoder, and writes 8-bit data (lower 8 bits: D7 to D0) of the shift register into an internal data latch selected by the latched address.
18 19 2 3 4 5 6 7 8 9 12 13	AO ₁ AO ₂ AO ₃ AO ₄ AO ₅ AO ₆ AO ₇ AO ₈ AO ₉ AO ₁₀ AO ₁₁ AO ₁₂	0	8-bit D/A output pins with OP amps.
11	Vcc	_	MCU interface and OP amp power supply pin.
20	GND	_	MCU interface and OP amp ground pin.
10	V _{DD}	_	D/A converter power supply pin.
1	Vss	_	D/A converter ground pin.

■ BLOCK DIAGRAM

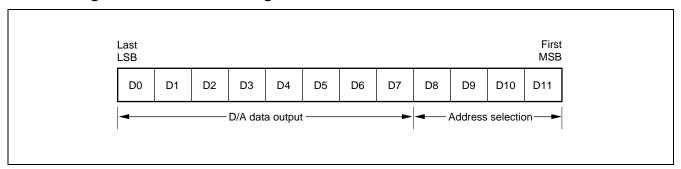


■ DATA CONFIGURATION

The MB88346L has a 12-bit shift register for controlling the chip. The data passed to the 12-bit shift register needs to be supplied in the following format.

The data structure consists of a total of 12 bits, four for address selection and eight for D/A data output.

1. Shift Register Control Data Configuration



2. D/A Converter Control Signals

D0	D1	D2	D3	D4	D5	D6	D7	D/A data output
0	0	0	0	0	0	0	0	≑ Vss
1	0	0	0	0	0	0	0	
0	1	0	0	0	0	0	0	
•	•	•	•	•	•	•	•	•
0	1	1	1	1	1	1	1	
1	1	1	1	1	1	1	1	÷ V _{DD}

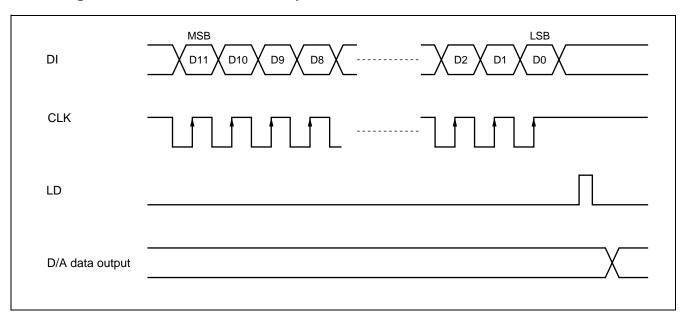
 $V_{LB} = (V_{DD} - V_{SS})/255$

3. Address Selection Signals

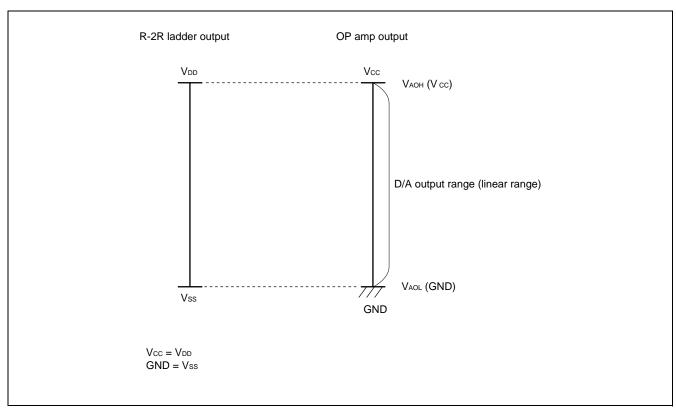
D8	D9	D10	D11	Address selection	
0	0	0	0	Don't Care	
0	0	0	1	AO ₁ selection	
0	0	1	0	AO ₂ selection	
0	0	1	1	AO ₃ selection	
0	1	0	0	AO ₄ selection	
0	1	0	1	AO ₅ selection	
0	1	1	0	AO ₆ selection	
0	1	1	1	AO ₇ selection	
1	0	0	0	AO ₈ selection	
1	0	0	1	AO ₉ selection	
1	0	1	0	AO ₁₀ selection	
1	0	1	1	AO ₁₁ selection	
1	1	0	0	AO ₁₂ selection	
1	1	0	1	Don't Care	
1	1	1	0	Don't Care	
1	1	1	1	Don't Care	

■ OPERATING DESCRIPTION

1. Timing Chart for Data Condition Setup



2. Analog Output Voltage Range



■ ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Condition	Rat	Unit	
Farameter	Syllibol	Condition	Min	Max	Offic
Power supply veltage	Vcc		- 0.3	+ 7.0	V
Power supply voltage	V _{DD} *	GND used as reference,	- 0.3	+ 7.0	V
Input voltage	Vin	Ta = + 25 °C	- 0.3	Vcc + 0.3	V
Output voltage	Vоит		- 0.3	Vcc + 0.3	V
Power consumption	P□	_		250	mW
Operating temperature	Та	_	- 20	+ 85	°C
Storage temperature	Tstg	_	– 55	+ 150	°C

^{*:} $V_{CC} \ge V_{DD}$

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

■ RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Condition			Unit	
raiametei	Syllibol	Condition	Min	Тур	Max	Offic
Power supply voltage 1	Vcc	_	2.7	_	3.6	V
Fower supply voltage 1	GND		_	0	_	V
Power cumply voltage 2	V _{DD}	V _{DD} – Vss ≥ 2.0 V	2.0	_	Vcc	V
Power supply voltage 2	Vss	VDD - VSS ≥ 2.0 V	GND	_	Vcc - 2.0	V
Analog output source current	IAL	Vcc = 3.0 V	_	_	1.0	mA
Analog output sink current	Іан	Vcc = 3.0 V	_	_	1.0	mA
Oscillator limiting output capacity	Cal		_	_	0.1	μF
Digital data value range	_	_	#00	_	#FF	_
Operating temperature	Та	_	- 20		+ 85	°C

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their representatives beforehand.

■ ELECTRICAL CHARACTERISTICS

1. DC Characteristics

(1) Digital Block

(VDD, VCC = 2.7 V to 3.6 V (VCC \geq VDD) , GND = Vss = 0 V, Ta = -20 °C to +85 °C)

Parameter	Symbol	Pin	Condition		Unit		
raiametei	Syllibol	FIII	Condition	Min	Тур	Max	Oilit
Power supply voltage	Vcc		_	2.7	3.0	3.6	V
Power supply current 1	Icc	Vcc	Stationary (CLK signal stopped) , no load	_	1.2	3.0	mA
Input leak current	IILK	0114 51	V _{IN} = 0 to V _{CC}	- 10		+ 10	μΑ
L level input voltage	VIL	CLK, DI, LD	_	_		0.2 Vcc	V
H level input voltage	Vін		_	0.8 Vcc		_	V
L level output voltage	Vol	DO	IoL = 2.5 mA	_		0.4	V
H level output voltage	Vон	ЪО	I он = $-400 \mu A$	Vcc - 0.4			V

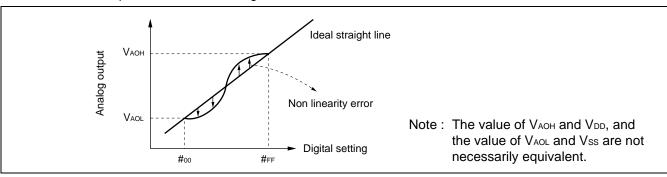
(2) Analog Block 1

(Vdb, Vcc = 2.7 V to 3.6 V (Vcc \geq Vdb) , GND = Vs = 0 V, Ta = -20 °C to +85 °C)

Parameter	Symbol	Pin	Condition		Unit		
Farameter	Syllibol Pill		Condition	Min	Тур	Max	Onit
Power consumption	l _{DD}	V _{DD}	Maximum setting value from #00 to #FF	_	0.6	1.5	mA
Analogyaltaga	V _{DD}	V _{DD}	$V_{DD} - V_{SS} > 2.0$	2.0	_	Vcc	V
Analog voltage	Vss	Vss	VDD - VSS ≥ 2.0	GND		Vcc - 2.0	V
Resolution	Res		_		8	_	bit
Monotonic increase	Rem	ΛΟ, to ΛΟ,	., ., ., .,		8	_	bit
Nonlinearity error	LE	LE AO1 10 AO12	$V_{DD} \le V_{CC} - 0.1 \text{ V},$ $V_{SS} \ge 0.1 \text{ V}, \text{ no load}$	– 1.5		+ 1.5	LSB
Differential linearity error	DLE		7 00 = 0 11 7 , 11 0 1 0 0 0	- 1.0		+ 1.0	LSB

Nonlinearity error: Deviation (error) in input/output curves with respect to an ideal straight line connecting output voltage at "00" and output voltage at "FF."

Differential linearity error: Deviation (error) in amplification with respect to theoretical increase in amplification per 1-bit increase in digital value.



(3) Analog Block 2

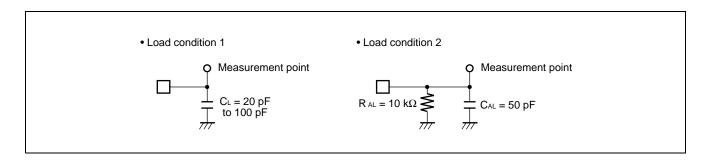
(VDD, VCC = 2.7 V to 3.6 V (VCC \geq VDD) , GND = Vss = 0 V, Ta = -20 °C to +85 °C)

Banamatan	Comple of	D:	Con dition		Value		I In it		
Parameter	Symbol	Pin	Condition	Min	Тур	Max	Unit		
Output minimum voltage 1	V _A OL1		$\begin{split} \text{V}_{\text{DD}} &= \text{V}_{\text{CC}} = 3.0 \text{ V}, \\ \text{V}_{\text{SS}} &= \text{GND} = 0.0 \text{ V}, \\ \text{I}_{\text{AL}} &= 0 \mu\text{A} \\ \text{Digital data} &= \#00 \end{split}$	Vss	—	Vss + 0.1	V		
Output minimum voltage 2	V _A OL2		$\begin{aligned} &V_{\text{DD}} = V_{\text{CC}} = 3.0 \text{ V}, \\ &V_{\text{SS}} = GND = 0.0 \text{ V}, \\ &I_{\text{AL}} = 500 \mu\text{A} \\ &\text{Digital data} = \#00 \end{aligned}$	Vss - 0.2	Vss	Vss + 0.2	V		
Output minimum voltage 3	V _A OL3				$\begin{aligned} &V_{\text{DD}} = V_{\text{CC}} = 3.0 \text{ V}, \\ &V_{\text{SS}} = GND = 0.0 \text{ V}, \\ &I_{\text{AH}} = 500 \mu\text{A} \\ &\text{Digital data} = \#00 \end{aligned}$	Vss	_	Vss + 0.2	V
Output minimum voltage 4	V _{AOL4}		$\begin{split} V_{\text{DD}} &= V_{\text{CC}} = 3.0 \text{ V}, \\ V_{\text{SS}} &= \text{GND} = 0.0 \text{ V}, \\ I_{\text{AL}} &= 1.0 \text{ mA} \\ \text{Digital data} &= \#00 \end{split}$	Vss - 0.3	Vss	Vss + 0.3	V		
Output minimum voltage 5	V _A OL5	AO1 to AO12	$\begin{aligned} &V_{DD} = V_{CC} = 3.0 \text{ V}, \\ &V_{SS} = GND = 0.0 \text{ V}, \\ &I_{AH} = 1.0 \text{ mA} \\ &Digital \text{ data} = \#00 \end{aligned}$	Vss	_	Vss + 0.3	V		
Output maximum voltage 1	Vаон1	A01 to A012	$\begin{aligned} &V_{DD} = V_{CC} = 3.0 \text{ V}, \\ &V_{SS} = GND = 0.0 \text{ V}, \\ &I_{AL} = 0 \mu\text{A} \\ &Digital \text{data} = \#FF \end{aligned}$	V _{DD} - 0.1		V _{DD}	V		
Output maximum voltage 2	V _A OH2		$\begin{split} &V_{\text{DD}} = V_{\text{CC}} = 3.0 \text{ V}, \\ &V_{\text{SS}} = GND = 0.0 \text{ V}, \\ &I_{\text{AL}} = 500 \mu\text{A} \\ &\text{Digital data} = \#FF \end{split}$	V _{DD} - 0.2	_	V _{DD}	V		
Output maximum voltage 3	Vаонз		$\begin{aligned} &V_{DD} = V_{CC} = 3.0 \text{ V}, \\ &V_{SS} = GND = 0.0 \text{ V}, \\ &I_{AH} = 500 \mu\text{A} \\ &Digital \text{data} = \#\text{FF} \end{aligned}$	V _{DD} - 0.2	V_{DD}	V _{DD} + 0.2	V		
Output maximum voltage 4	Vаон4		$\begin{split} &V_{\text{DD}} = V_{\text{CC}} = 3.0 \text{ V}, \\ &V_{\text{SS}} = \text{GND} = 0.0 \text{ V}, \\ &I_{\text{AL}} = 1.0 \text{ mA} \\ &\text{Digital data} = \#\text{FF} \end{split}$	V _{DD} - 0.3	_	V _{DD}	V		
Output maximum voltage 5	V _A OH5		$\begin{split} &V_{\text{DD}} = V_{\text{CC}} = 3.0 \text{ V}, \\ &V_{\text{SS}} = \text{GND} = 0.0 \text{ V}, \\ &I_{\text{AH}} = 1.0 \text{ mA} \\ &\text{Digital data} = \#\text{FF} \end{split}$	V _{DD} - 0.3	V _{DD}	V _{DD} + 0.3	V		

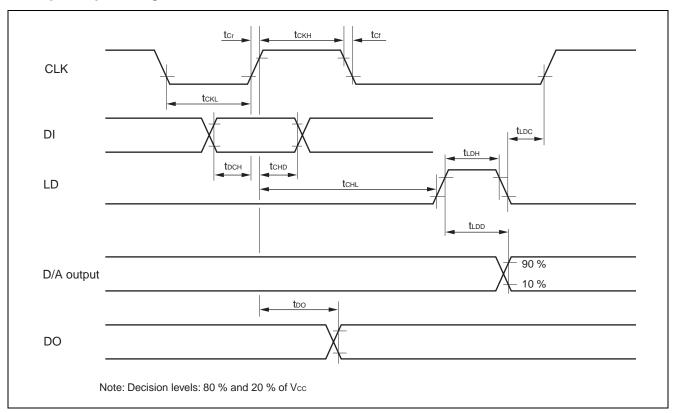
2. AC Characteristics

(Vdb, Vcc = 2.7 V to 3.6 V (Vcc \geq Vdb) , GND = Vss = 0 V, Ta = - 20 °C to +85 °C)

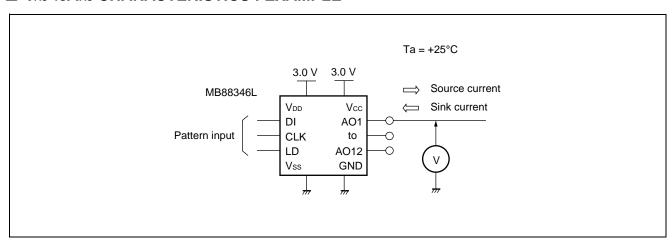
Parameter	Symbol	Condition	Va	Unit	
Farameter	Symbol		Min	Max	Onit
Clock L level pulse width	t ckl	_	200	_	ns
Clock H level pulse width	t ckH	_	200	_	ns
Clock rise time Clock fall time	tcr tcf	_	_	200	ns
Data setup time	tосн	_	30	_	ns
Data hold time	t CHD	_	60	_	ns
Load setup time	t chL	_	200	_	ns
Load hold time	t ldc	_	100	_	ns
Load H level pulse width	t LDH	_	100	_	ns
Data output delay time	t₀o	Refer to "• Load condition 1"	70	600	ns
D/A output settling time	t LDD	Refer to "• Load condition 2"		300	μS



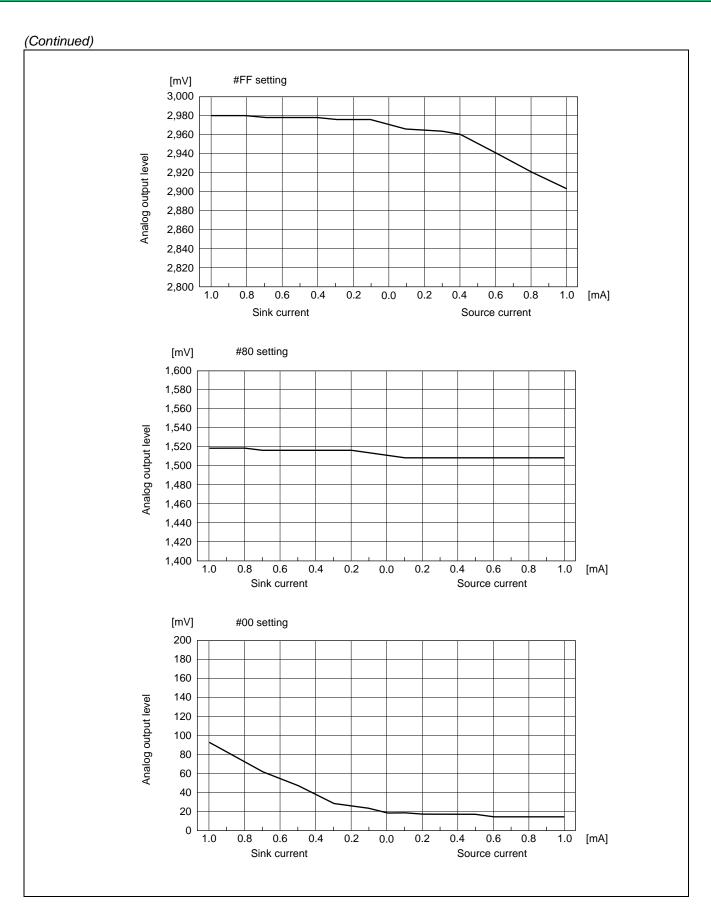
• Input/output timing



■ Vao vs. Iao CHARACTERISTICS : EXAMPLE



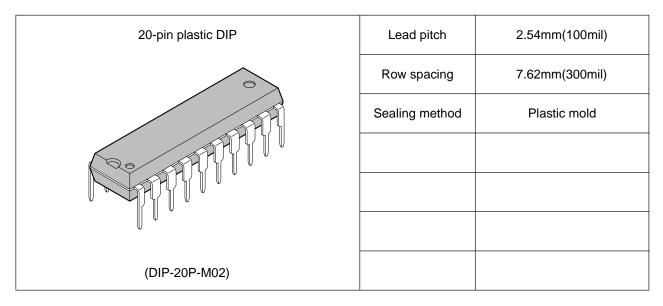
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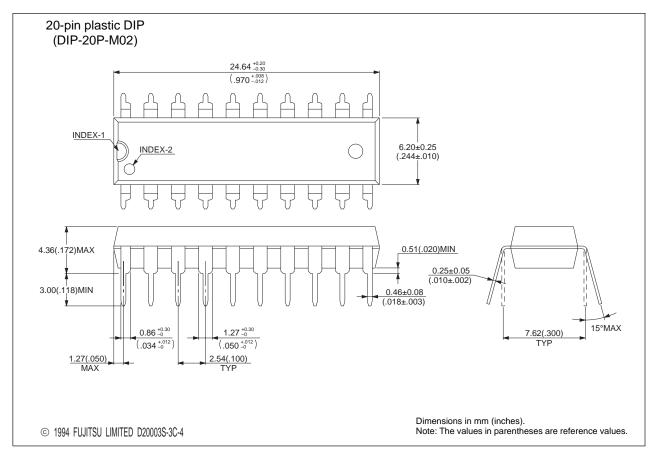


■ ORDERING INFORMATION

Part number	Package	Remarks
MB88346LP	20-pin plastic DIP (DIP-20P-M02)	
MB88346LPFV	20-pin plastic SSOP (FPT-20P-M03)	

■ PACKAGE DIMENSIONS

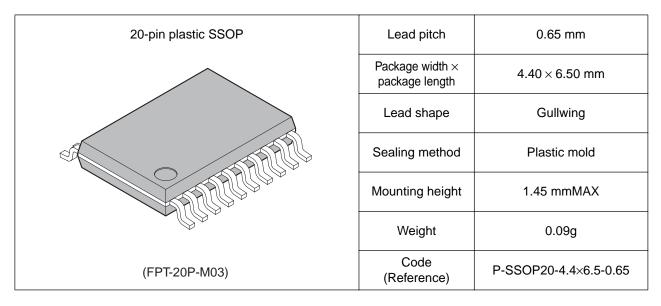


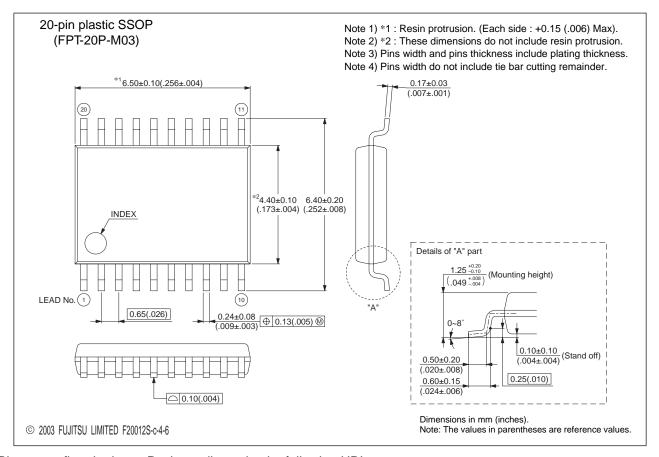


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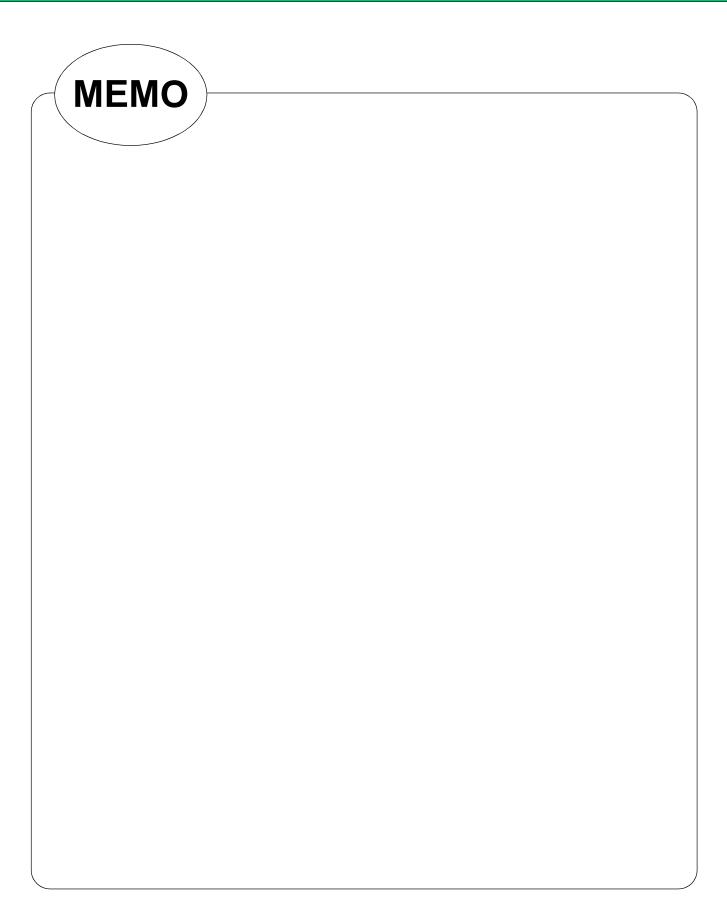
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